Silicon PNP Power Transistors 2SA1306 2SA1306A 2SA1306B

DESCRIPTION

·With TO-220Fa package
·Complement to type
2SC3298,2SC3298A,2SC3298B

APPLICATIONS

·Power amplifier applications
·Driver stage amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

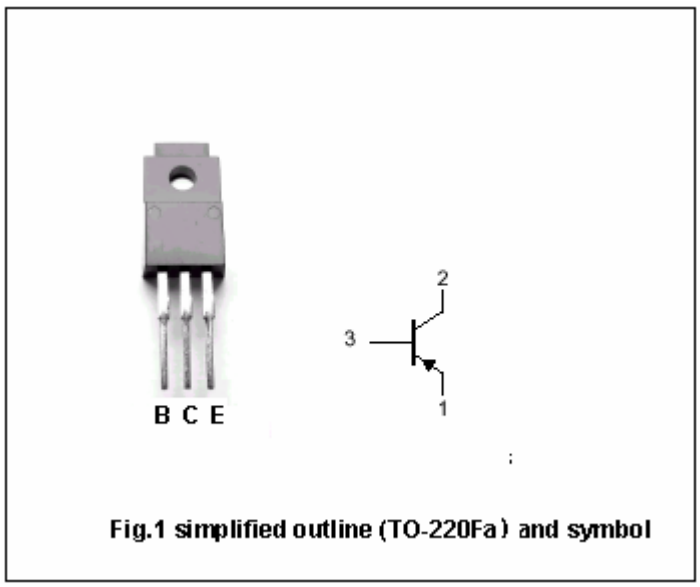

Fig.1 simplified outline (TO-220Fa) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA1306	Open emitter	-160	V
		2SA1306A		-180	
		2SA1306B		-200	
V_{CEO}	Collector-emitter voltage	2SA1306	Open base	-160	V
		2SA1306A		-180	
		2SA1306B		-200	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-1.5	A
I_B	Base current			-0.15	A
P_C	Collector power dissipation		T_C=25□	20	W
T_j	Junction temperature			150	□
T_{stg}	Storage temperature			-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SA1306	I_C=10mA , I_B=0	-160			V
		2SA1306A		-180			
		2SA1306B		-200			
V_{CEsat}	Collector-emitter saturation voltage		I_C=-0.5A, I_B=-50mA			-1.5	V
V_{BE}	Base-emitter voltage		I_C=-0.5A ,V_{CE}=-5V			-1.0	V
I_{CBO}	Collector cut-off current		V_{CB}=-160V, I_E=0			-1.0	μA
I_{EBO}	Emitter cut-off current		V_{EB}=-5V; I_C=0			-1.0	μA
h_{FE}	DC current gain		I_C=-0.1A ; V_{CE}=-5V	70		240	
C_{ob}	Output capacitance		I_E=0 ; V_{CB}=-10V,f=1MHz		30		pF
f_T	Transition frequency		I_C=-0.1A ; V_{CE}=-10V		100		MHz

◆ **h_{FE} Classifications**

O	Y
70-140	120-240

PACKAGE OUTLINE

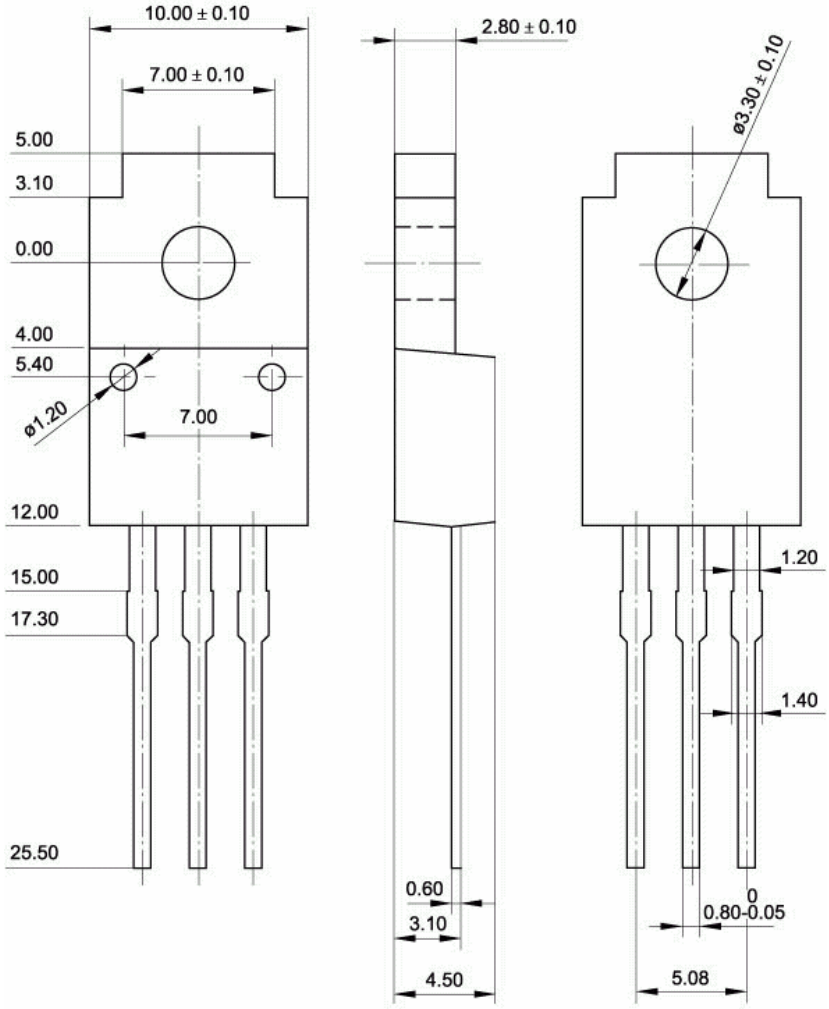

Fig.2 Outline dimensions (unindicated tolerance:±0.15 mm)